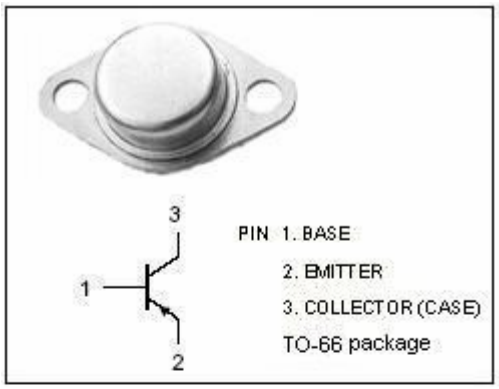
isc Silicon PNP Power Transistor 2SA483

DESCRIPTION

- High Collector Current:: I_C= -1.5A
- Collector-Emitter Breakdown Voltage
  : $V_{(BR)CEO}$= -150V(Min)
- Complement to Type 2SC783

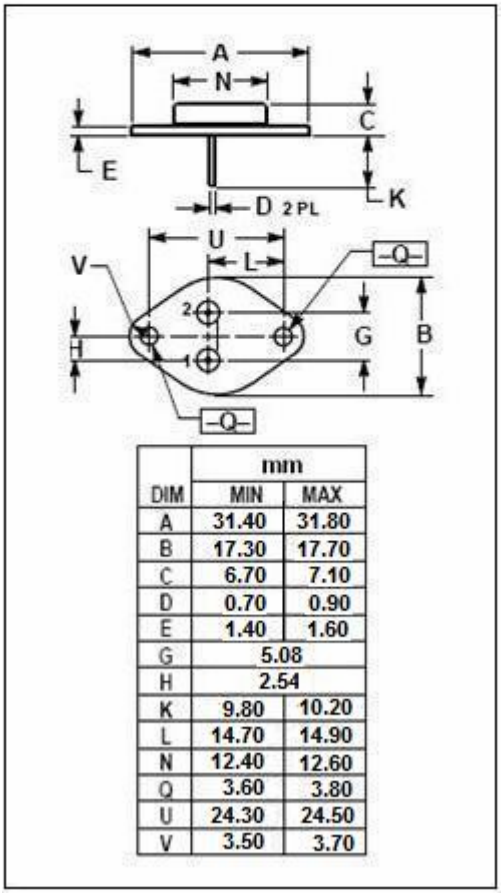


APPLICATIONS

- Power amplifier applications
- Vertical output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_E	Emitter Current-Continuous	1.5	A
P_C	Total Power Dissipation @ T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -0.5mA ; I_E= 0	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A ; V_{CE}= -10V			-1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V ; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-100	μA
h_{FE}	DC Current Gain	I_C= -0.1A ; V_{CE}= -10V	30		240	
f_T	Current-Gain—Bandwidth Product	I_C= -0.1A ; V_{CE}= -10V		10		MHz
C_{OB}	Output Capacitance	V_{CB}= -10V; f_{test}= 1MHz		50		pF

◆ **h_{FE-1} Classifications**

R	O	Y
30-80	70-140	120-240